



Note:

1. SUBSTRATE:IR MONO GRADE SI
2. GROWING METHOD:CZ
3. CLEAR APERTURE:90%
4. SURFACE QUALITY:S1&S2 60-40 SCRATCH-DIG
5. PARALLELISM:3ARCMIN
6. PV:1λ
7. COATING:NONE

8 FINE GRIND SURFACE

SPECIFICATIONS SUBJECT TO CHANGE  
WITHOUT NOTICE

FOR INFORMATION ONLY  
NOT FOR MANUFACTURE

DRAWING PROJECTION		ALL DIMS IN		MM	
DESIGNED	CHECKED	APPROVED		SCALE	
				1:1	
MATERIAL	Silicon	TITLE	SI IR-MONO ROUND WINDOW ∅41*T3		
本征晶体 INTRINSIC CRYSTAL	www.icc-mall.com	DWG NO	PSI01F005		
		EDITION	1ST	SHEET	1/1